



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

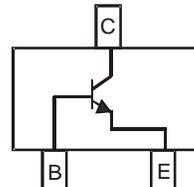
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type Available (NK-DSS20200L)
- Ultra Low Collector-Emitter Saturation Voltage

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	4	A
Continuous Collector Current	I_C	2	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	209	$^\circ\text{C/W}$
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	1.2	mW
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	104	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	20	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	—	100	nA	$V_{CB} = 20\text{V}, I_E = 0$
Emitter-Base Cutoff Current	I_{EBO}	—	—	100	nA	$V_{EB} = 6\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 5)						
DC Current Gain	h_{FE}	200	—	—	—	$V_{CE} = 2\text{V}, I_C = 10\text{mA}$
		200	330	—		$V_{CE} = 2\text{V}, I_C = 500\text{mA}$
		200	—	—		$V_{CE} = 2\text{V}, I_C = 1\text{A}$
		200	—	—		$V_{CE} = 2\text{V}, I_C = 2\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	10	mV	$I_C = 0.1\text{A}, I_B = 10\text{mA}$
		—	40	50		$I_C = 1.0\text{A}, I_B = 100\text{mA}$
		—	75	90		$I_C = 1.0\text{A}, I_B = 10\text{mA}$
		—	70	100		$I_C = 2.0\text{A}, I_B = 200\text{mA}$
Equivalent On-Resistance	$R_{CE(SAT)}$	—	35	50	m Ω	$I_E = 2\text{A}, I_B = 200\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	0.9	V	$I_C = 1\text{A}, I_B = 10\text{mA}$
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	0.9	V	$V_{CE} = 2\text{V}, I_C = 1\text{A}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	150	—	—	MHz	$V_{CE} = 5\text{V}, I_C = 100\text{mA}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	45	pF	$V_{CB} = 3\text{V}, f = 1\text{MHz}$
Input Capacitance	C_{ibo}	—	—	450	pF	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}$
SWITCHING CHARACTERISTICS						
Turn-On Time	t_{on}	—	—	200	ns	$V_{CC} = 15\text{V}, I_C = 750\text{mA}, I_{B1} = 15\text{mA}$
Delay Time	t_d	—	—	100	ns	
Rise Time	t_r	—	—	100	ns	
Turn-Off Time	t_{off}	—	—	610	ns	$V_{CC} = 15\text{V}, I_C = 750\text{mA}, I_{B1} = I_{B2} = 15\text{mA}$
Storage Time	t_s	—	—	500	ns	
Fall Time	t_f	—	—	110	ns	

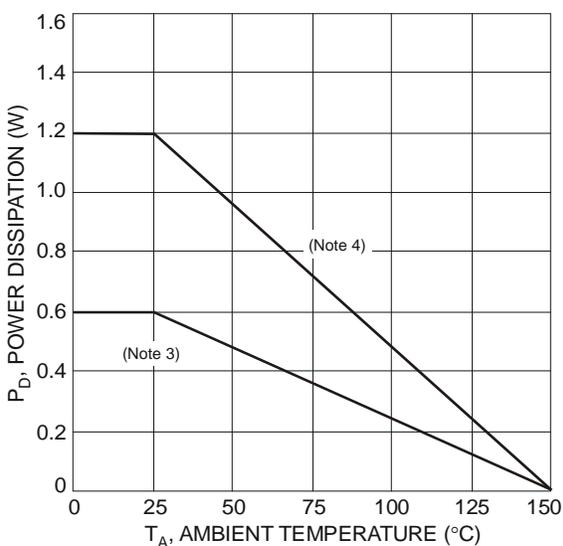
 Notes: 5. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.


Fig. 1 Power Dissipation vs. Ambient Temperature

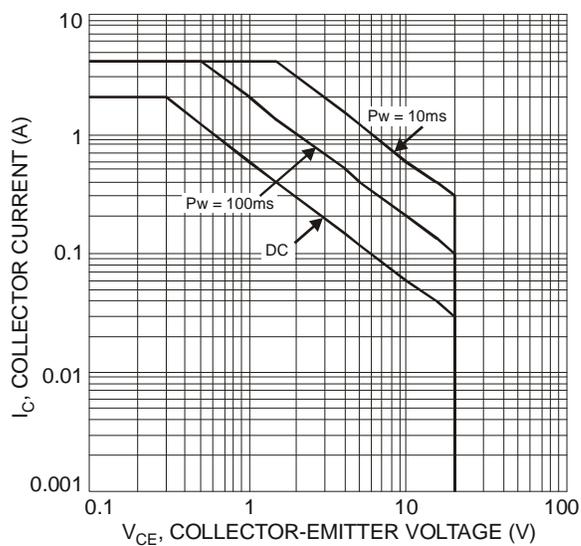


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

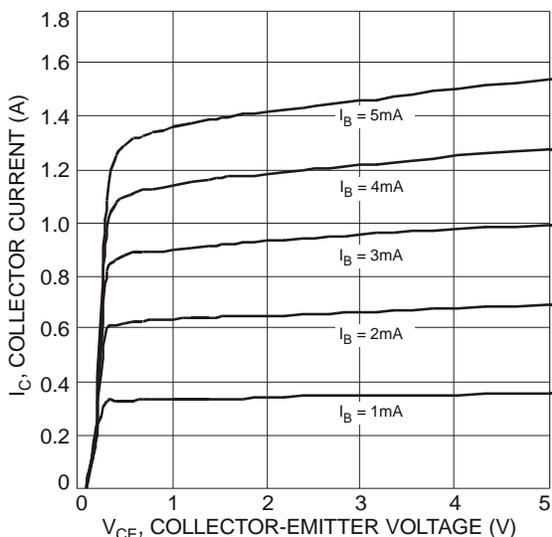


Fig. 3 Typical Collector Current vs. Collector-Emitter Voltage

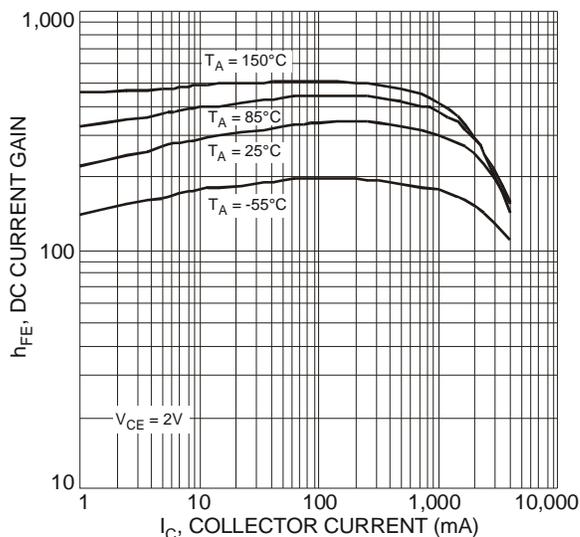


Fig. 4 Typical DC Current Gain vs. Collector Current

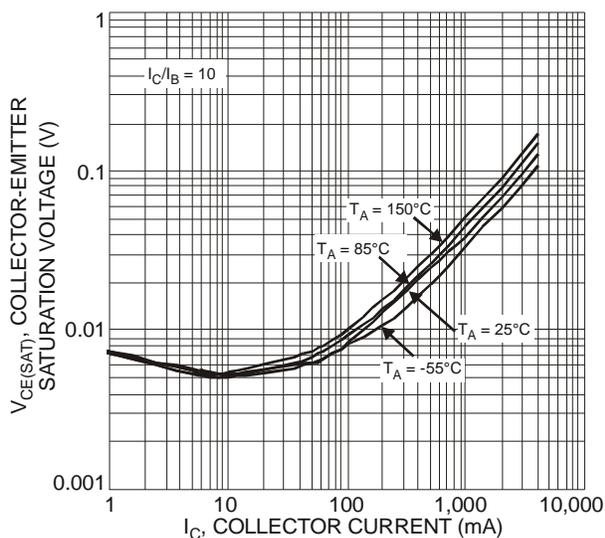


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

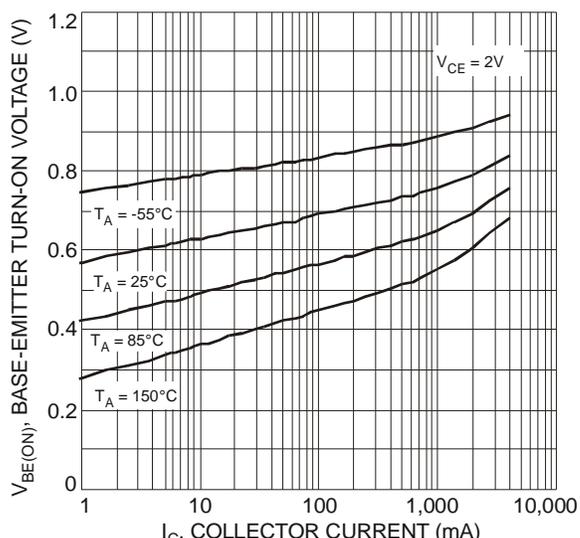


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

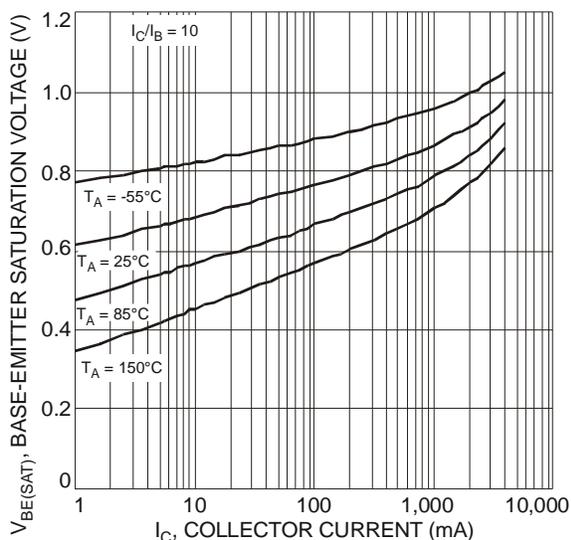


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

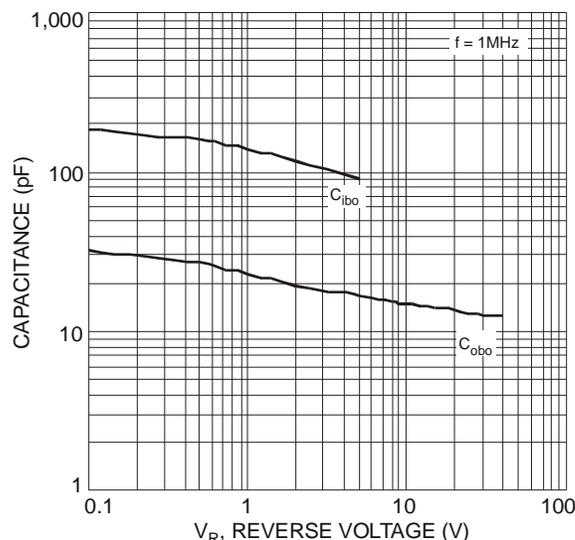


Fig. 8 Typical Capacitance Characteristics

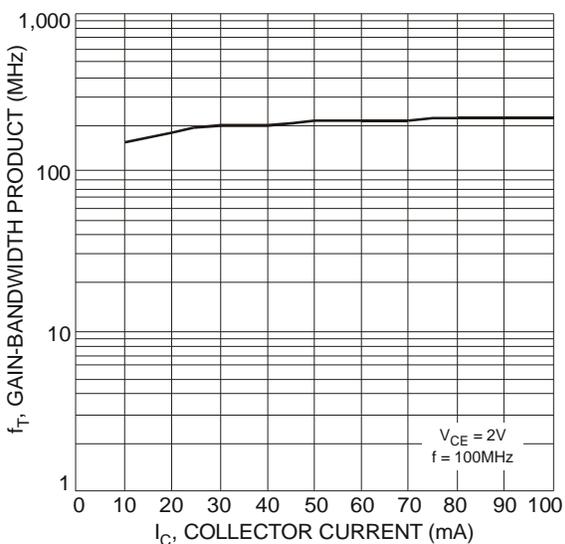


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

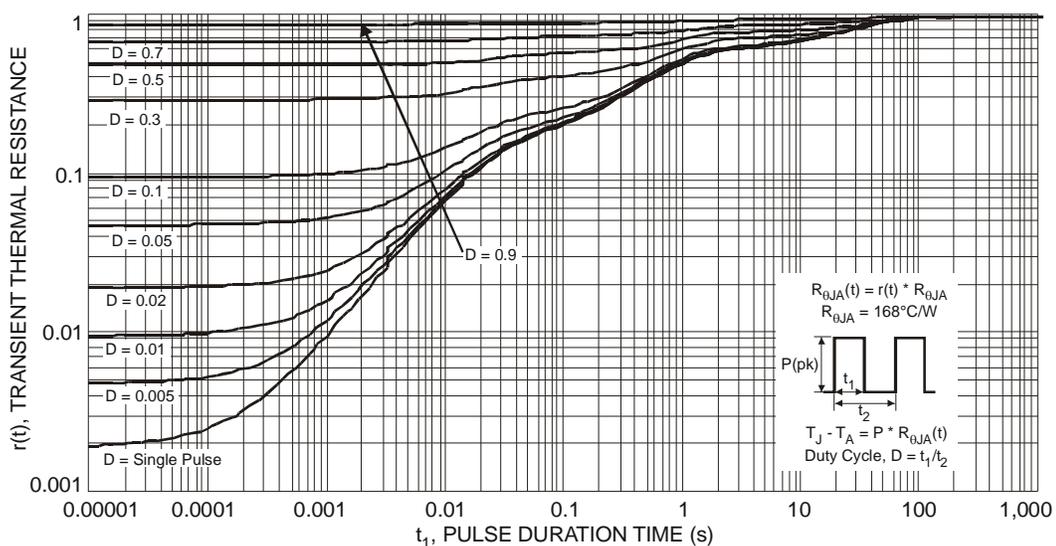
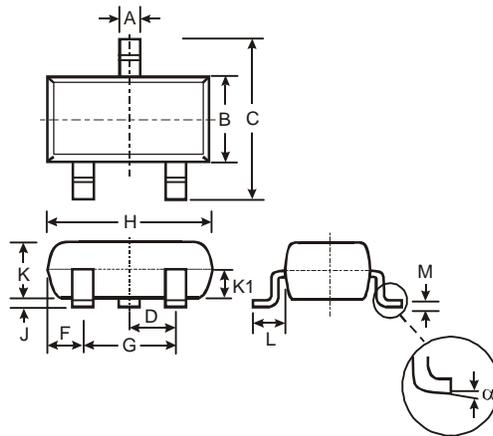


Fig. 10 Transient Thermal Response

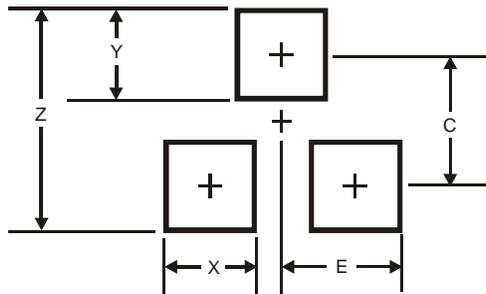
Package Outline Dimensions



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35